**Vishay Siliconix** 

ROHS COMPLIANT

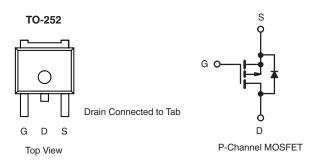
HALOGEN

FREE



## Automotive P-Channel 40 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	- 40				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0094				
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$	0.0190				
I <sub>D</sub> (A)	- 50				
Configuration	Single				



#### FEATURES

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFET
- Package with Low Thermal Resistance
- Compliant to RoHS Directive 2002/95/EC
- AEC-Q101 Qualified<sup>d</sup>
- Find out more about Vishay's Automotive Grade Product Requirements at: <u>www.vishay.com/applications</u>

ORDERING INFORMATION	
Package	TO-252
Lead (Pb)-free and Halogen-free	SQD50P04-09L-GE3

ABSOLUTE MAXIMUM RATINGS (T	<sub>C</sub> = 25 °C, unles	s otherwise noted	4)		
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V <sub>DS</sub>	- 40	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20	v	
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 25 °C	- I <sub>D</sub>	- 50		
Continuous Drain Current <sup>a</sup>	T <sub>C</sub> = 125 °C		- 50		
Continuous Source Current (Diode Conduction) <sup>a</sup>	IS	- 50	А		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	- 200		
Single Pulse Avalanche Current	L = 0.1 mH	I <sub>AS</sub>	- 50		
Single Pulse Avalanche Energy	L = 0.1 IIIH	E <sub>AS</sub>	125	mJ	
Mauina David Diasia atianh	T <sub>C</sub> = 25 °C	D	136	W	
Maximum Power Dissipation <sup>b</sup>	T <sub>C</sub> = 125 °C	P <sub>D</sub>	45	٧V	
Operating Junction and Storage Temperature Rar	nge	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient F	PCB Mount <sup>c</sup>	R <sub>thJA</sub>	50	°C ///
Junction-to-Case (Drain)		R <sub>thJC</sub>	1.1 °C/W	

#### Notes

a. Package limited.

b. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

c. When mounted on 1" square PCB (FR-4 material).

d. Parametric verification ongoing.

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PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT	
Static	•							
Drain-Source Breakdown Voltage	V <sub>DS</sub>	V <sub>GS</sub> =	V <sub>GS</sub> = 0 V, I <sub>D</sub> = - 250 μA		-	-	v	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = - 250 μA	- 1.5	-	- 2.5	v	
Gate-Source Leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = - 40 V	-	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{GS} = 0 V$	$V_{DS} = -40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	- 50	μA	
		$V_{GS} = 0 V$	$V_{DS}$ = - 40 V, T <sub>J</sub> = 175 °C	-	-	- 150		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = - 10 V	$V_{DS} \le$ - 5 V	- 50	-	-	Α	
		V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 17 A	-	0.0076	0.0094	Ω	
Drain Course On State Desistence?	Р	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 50 A, T <sub>J</sub> = 125 °C	-	-	0.014		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 10 V	I <sub>D</sub> = - 50 A, T <sub>J</sub> = 175 °C	-	-	0.017		
		V <sub>GS</sub> = - 4.5 V	I <sub>D</sub> = - 14 A	-	0.012	0.019		
Forward Transconductanceb	9 <sub>fs</sub>	V <sub>DS</sub> = - 15 V, I <sub>D</sub> = - 17 A		-	46	-	S	
Dynamic <sup>b</sup>		- -						
Input Capacitance	C <sub>iss</sub>			-	5339	6675		
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	<sub>S</sub> = 0 V V <sub>DS</sub> = - 20 V, f = 1 MHz		852	1065	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			-	681	855		
Total Gate Charge <sup>c</sup>	Qg			-	103	155		
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = - 10 V	V <sub>GS</sub> = - 10 V V <sub>DS</sub> = - 20 V, I <sub>D</sub> = - 50 A		24	-	nC	
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>	1   [		-	16	-		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = -20 \text{ V}, \text{ R}_{\text{L}} = 0.4 \Omega$ $\text{I}_{\text{D}} \cong -50 \text{ A}, \text{ V}_{\text{GEN}} = -10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		-	13	20		
Rise Time <sup>c</sup>	t <sub>r</sub>			-	15	23	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>			-	61	92		
Fall Time <sup>c</sup>	t <sub>f</sub>			-	19	29		
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>							
Pulsed Current <sup>a</sup>	I <sub>SM</sub>				-	- 200	А	
Forward Voltage	V <sub>SD</sub>	I <sub>F</sub> = -	- 50 A, V <sub>GS</sub> = 0 V	-	- 0.95	- 1.5	V	

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$ 

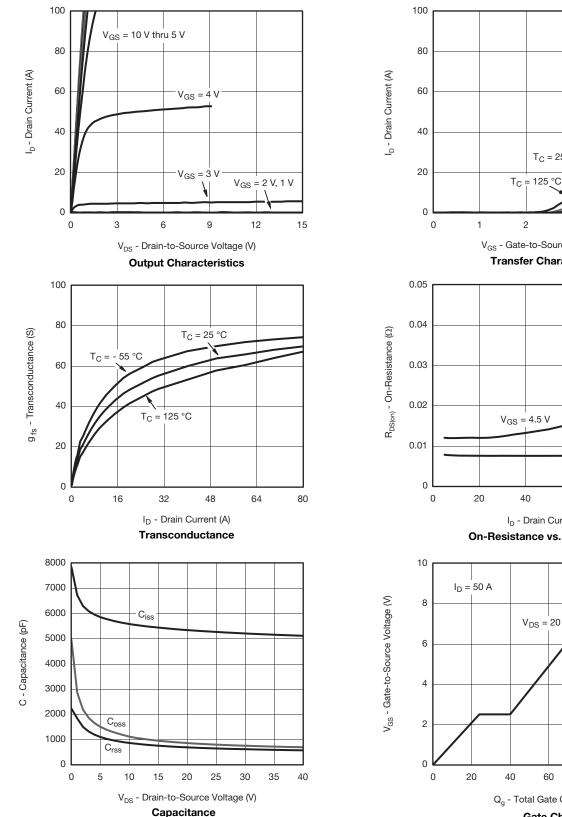
b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

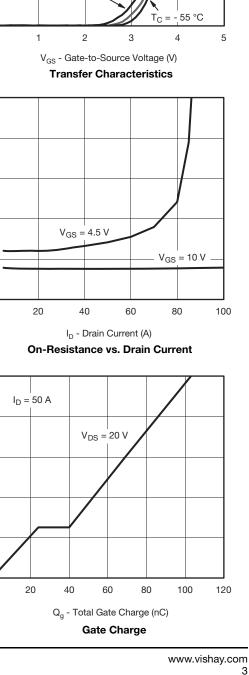


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### **TYPICAL CHARACTERISTICS** ( $T_A = 25$ °C, unless otherwise noted)

Document Number: 65018 S10-1996-Rev. B, 20-Sep-10

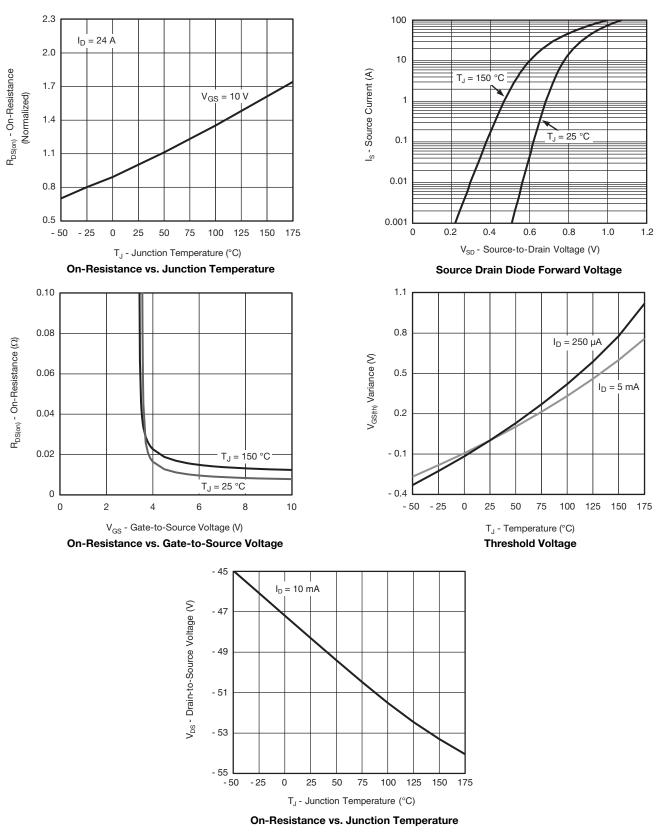


T<sub>C</sub> = 25

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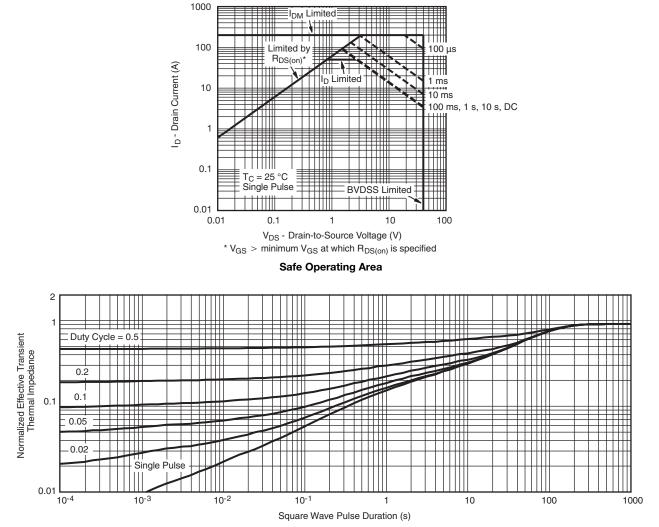
#### TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)





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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

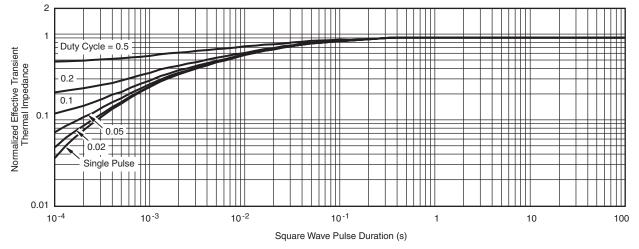


Normalized Thermal Transient Impedance, Junction-to-Ambient

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#### **THERMAL RATINGS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

The characteristics shown in the two graphs

- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)

- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

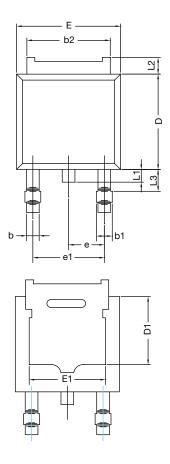
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?65018">www.vishay.com/ppg?65018</a>.

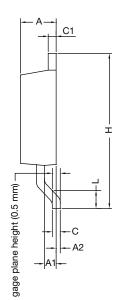


# Package Information

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#### **TO-252AA CASE OUTLINE**





	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
E	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28	BSC	0.090 BSC		
e1	4.57	BSC	0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11- DWG: 534	0110-Rev. L, <sup>-</sup> 7	18-Apr-11			

Note

• Dimension L3 is for reference only.

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#### **RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)**



Recommended Minimum Pads Dimensions in Inches/(mm)

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